

**AMENDMENTS TO THE CLAIMS**

Please add new claims 13 and 14 in accordance with the following list of claims

1. (Original) A semiconductor light emitting device comprising:  
a semiconductor substrate;  
a semiconductor laminating portion formed on said semiconductor substrate,  
said semiconductor laminating portion including a light emitting layer forming portion  
having at least an n-type layer and a p-type layer;  
a current diffusing electrode formed on said semiconductor laminating portion,  
said current diffusing electrode exhibiting translucency and electric conductivity;  
a bonding electrode formed on a part of said current diffusing electrode; and  
an electrode formed on a rear surface of said semiconductor substrate,  
wherein said semiconductor laminating portion and said current diffusing  
electrode are separated into a plurality of light emitting unit portions, an electrode pad  
portion, and connecting portions for connecting between said electrode pad portion and  
said light emitting unit portions or between two of said light emitting unit portions, and  
wherein said bonding electrode is provided on said electrode pad portion, and  
said electrode pad portion is formed so as to make said light emitting layer forming portion  
in said electrode pad portion be nonluminous.

2. (Original) The semiconductor light emitting device of claim 1,  
wherein said connecting portions are formed so as to make said light emitting layer forming  
portion in each of said connecting portions be nonluminous.

3. (Original) The semiconductor light emitting device of claim 2,  
wherein a metallic electrode is formed on said current diffusing electrode of each of said  
connecting portions.

4. (Original) The semiconductor light emitting device of claim 1,  
wherein a current blocking layer is formed on one layer between said current diffusing  
electrode and said semiconductor substrate to be nonluminous.

5. (Original) The semiconductor light emitting device of claim 4, wherein said current blocking layer is an electrically-insulating layer, or a semiconductor layer that has different conductivity from that of semiconductor layers adjoining to said current blocking layer.

6. (Original) The semiconductor light emitting device of claim 1, wherein when the planar shape of each of said light emitting unit portions is circular, the size of each of said light emitting unit portions is defined such that the diameter thereof is not more than six times of the thickness of said semiconductor laminating portion.

7. (Original) The semiconductor light emitting device of claim 6, wherein the thickness of said semiconductor laminating portion is approximately 3 to 10  $\mu\text{m}$  and the diameter of each of said light emitting unit portions is approximately 10 to 50  $\mu\text{m}$ .

8. (Original) The semiconductor light emitting device of claim 1, wherein when the planar shape of each of said light emitting unit portions is rectangular or elliptic, the size of each of said light emitting unit portions is defined such that a longer side or a longer diameter thereof is not more than six times of the thickness of said semiconductor laminating portion.

9. (Original) The semiconductor light emitting device of claim 1, wherein a distance between adjoining two of said light emitting unit portions is defined to be not less than twice of the thickness of said semiconductor laminating portion.

10. (Original) The semiconductor light emitting device of claim 1, wherein said current diffusing electrode is made of an Au-Ge or Au-Ni alloy layer having a thickness of 2 to 100 nm.

11. (Original) The semiconductor light emitting device of claim 1, wherein said current diffusing electrode is an ITO film.

12. (Original) The semiconductor light emitting device of claim 1, wherein said semiconductor laminating portion is made of an InGaAlP based material or an AlGaAs based material.

13. (New) The semiconductor light emitting device of claim 1, further comprising a current blocking layer formed on one layer between said current diffusing electrode and said semiconductor substrate, in portions of said semiconductor laminating portion in which said light emitting layer forming portion is to be nonluminous.

14. (New) The semiconductor light emitting device of claim 13, wherein said current blocking layer is formed between said current diffusing layer and said light emitting layer forming portion.